Silicon PNP Power Transistors 2SA1308

DESCRIPTION

・With TO-220F package

・Low collector saturation voltage

APPLICATIONS

・High current switching applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

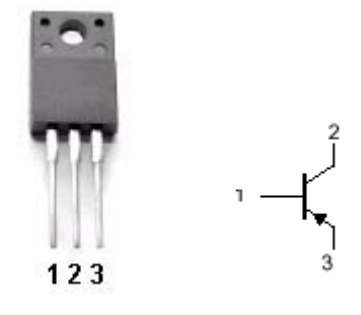


Fig.1 simplified outline (TO-220F) and symbol

Absolute maximum ratings (Ta=25℃)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-100	V
V_{CEO}	Collector-emitter voltage	Open base	-100	V
V_{EBO}	Emitter-base voltage	Open collector	-7	V
I_C	Collector current		-5	A
I_{CM}	Collector current-peak		-8	A
P_C	Collector dissipation	T_C=25℃	30	W
T_j	Junction temperature		150	℃
T_{stg}	Storage temperature		-55~150	℃

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CHARACTERISTICS

Tj=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA ; I_B=0	-100			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-3A;I_B=-0.15A			-0.4	V
V_{BEsat}	Base-emitter saturation voltage	I_C=-3A;I_B=-0.15A			-1.2	V
I_{CBO}	Collector cut-off current	V_{CB}=-100V;I_E=0			-1	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-7V; I_C=0			-1	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-1V	70		240	
h_{FE-2}	DC current gain	I_C=-3A ; V_{CE}=-1V	30			
f_T	Transition frequency	I_C=-1A ; V_{CE}=-4V		60		MHz
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V;f=1MHz		200		pF

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PACKAGE OUTLINE

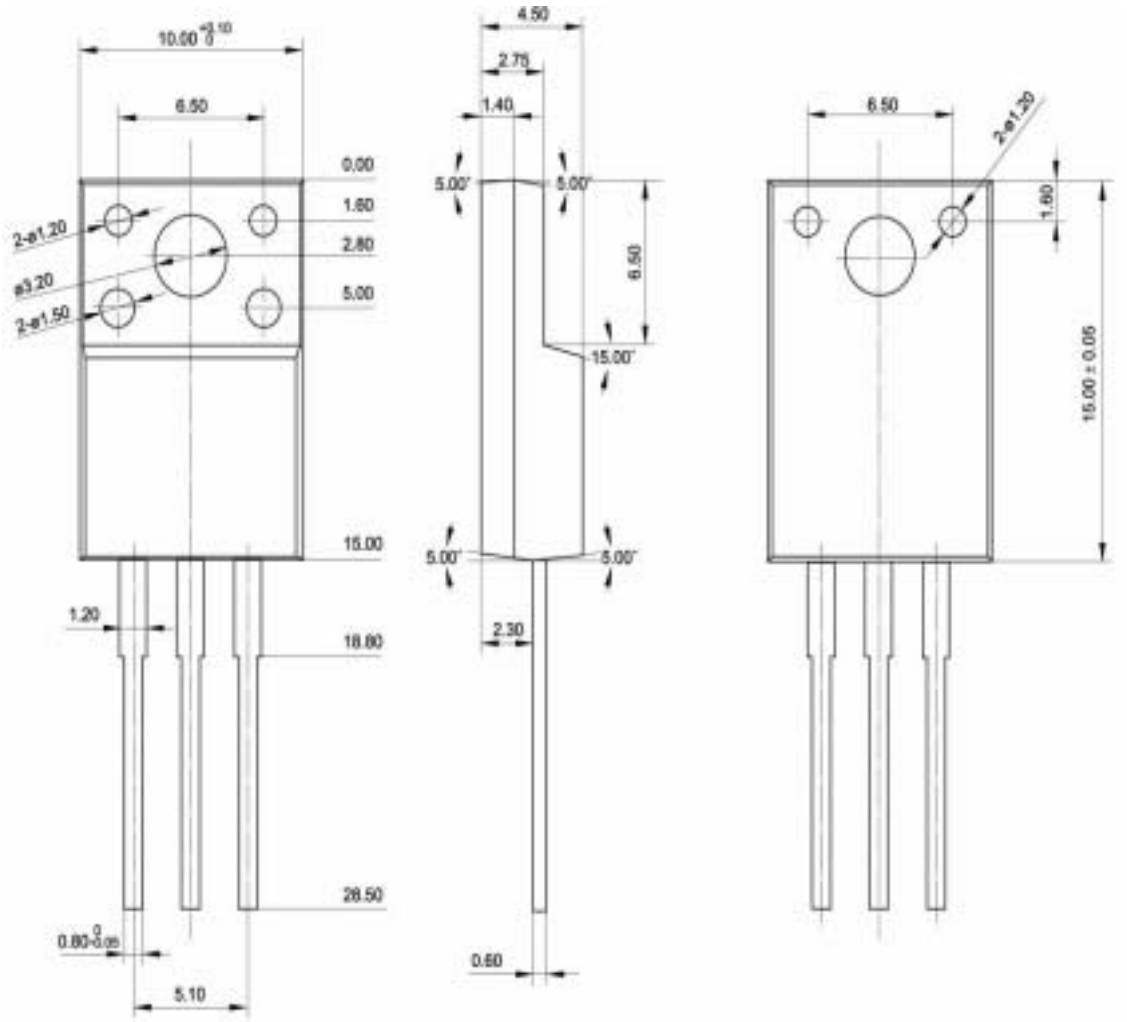


Fig.2 Outline dimensions